

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	309	(memory and logic adj1 device\$1).ti.	USPAT; US-PGP; UB; EPO; JPO; DERWEN T; IBM_TD; B	2002/03/31 16:56
2	BRS	L2	29246	first nearl transistor and second adj1 transistor	USPAT; US-PGP; UB; EPO; JPO; DERWEN T; IBM_TD; B	2002/03/31 16:47
3	BRS	L3	5	1 and 2	USPAT; US-PGP; UB; EPO; JPO; DERWEN T; IBM_TD; B	2002/03/31 16:47
4	BRS	L4	4674	memory nearl device\$1 and logic adj1 device\$1).ti.	USPAT; US-PGP; UB; EPO; JPO; DERWEN T; IBM_TD; B	2002/03/31 16:45
5	BRS	L5	48	(memory nearl device\$1 and logic adj1 device\$1).ti.	USPAT; US-PGP; UB; EPO; JPO; DERWEN T; IBM_TD; B	2002/03/31 16:56

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L6	9	5 and transistor	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 16:45
7	BRS	L7	3338	memory nearl device\$1 and logic adj1 devices1	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 16:57
8	BRS	L8	123	dual adj1 gate adj1 devices1	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 16:58
9	BRS	L9	16	7 and 8	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 16:58
10	BRS	L10	14	7 and 8 and 9	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 16:58

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L11	189164	date add1 oxides3)	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 17:06
12	BRS	L12	422	7 and 11	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 17:06
13	BRS	L13	109	date add1 oxides3) transistor	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 17:06
14	BRS	L14	53	13 and thickness	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD;	2002/03/31 17:06
15	BRS	L15	53	14 and (oxidation or oxides3)	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 17:06

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L16	11	15 and (high adj1 temperature)	JPO; DERWEN; T; IBM_TD; B	2002/03/31 17:13
17	BRS	L17	1694	((dielectric adj1 layer) near5 (gate adj1 oxides1)	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 17:22
18	BRS	L19	7	15 and 18	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 17:14
19	BRS	L20	893	((dielectric or silicon adj1 dioxide) adj1 layer) near5 (gate adj1 oxides1)	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 17:24

	Type	L #	Hits	Search Text	DBs	Time Stamp
21	BRS	L21	21	7 and 20	USPAT; US-PGP; UB; EPO; JPO; DERWEN	2002/03/31 17:27
22	BRS	L22	128	21 and transistor	USPAT; US-PGP; UB; EPO; JPO; DERWEN	2002/03/31 17:27
23	BRS	L23	1436	Advanced and multi-layered devices	USPAT; US-PGP; UB; EPO; JPO; DERWEN	2002/03/31 17:27
24	BRS	L24	193	7 and 23	USPAT; US-PGP; UB; EPO; JPO; DERWEN	2002/03/31 17:27
25	BRS	L25	1	Advanced and multi-layered	USPAT; US-PGP; UB; EPO; JPO; DERWEN	2002/03/31 17:27

	Type	L #	Hits	Search Text	DBs	Time Stamp
18	BRS	127	3	4551910.pn.	USPAT; US-PPG; UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 17:43
19	BRS	128	236	gate adjl oxide\$iti.	USPAT; US-PPG; UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 17:43
20	BRS	129	14	7 and 28	USPAT; US-PPG; UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 17:43
30	BRS	130	3	5057449.pn.	USPAT; US-PPG; UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 18:12

	Type	L #	Hits	Search Text	DBs	Time Stamp
					USPAT; US-PGP UB; EPO; JPO; DERWEN; T; IBM_TD; B	
32	BRS	L32	53	31 and 7	USPAT; US-PGP UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 18:47
33	BRS	L33	2	1 and (silicon adj1 nitride) near5 (oxidation)	USPAT; US-PGP UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 18:50
34	BRK	L34	1	7 and (silicon adj1 nitride) near5 (boron and oxidation)	USPAT; US-PGP UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 18:51
35	BRK	L35	0	7 and (silicon adj1 nitride) near5 (boron and oxidation)	USPAT; US-PGP UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 18:51

	Type	L #	Hits	Search Text	DBs	Time Stamp
36	BRS	L37	17	'7 and (silicon adj1 nitride) near5 (boron or oxidized)	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 18:51
37	BRS	L38	17	'7 and (silicon adj1 nitride) near3 (oxidized or oxidation)	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 18:51
38	BRS	L38	41	'7 and (silicon adj1 nitride) near3 (oxidized or oxidation)	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 19:26
39	BRS	L39	15	'7 and (silicon adj1 oxide) near3 (oxidized or oxidation)	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 19:29
40	BRS	L40	17	'7 and (silicon adj1 dioxide) near3 (oxidized or oxidation)	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B	2002/03/31 19:30

	Type	L #	Hits	Search Text	DBs	Time Stamp
41	BRS	L41	33	7 and (gate adj1 oxide) near3 (oxidized or oxidation)	USPAT; US-PGP; UB; EPO; JPO; DERWEN; TPM_TDI; B	2002/03/31 20:05
42	BRS	L42	14	41 and (high near1 temperature)	USPAT; US-PGP; UB; EPO; JPO; DERWEN; TPM_TDI; B	2002/03/31 20:05
43	BRS	L43	15	7 and (oxidized or dielectric) near1 (oxidation or oxidized)	USPAT; US-PGP; UB; EPO; JPO; DERWEN; TPM_TDI; B	2002/03/31 20:06
44	BRS	L44	75	43 and (high adj1 temperature)	USPAT; US-PGP; UB; EPO; JPO; DERWEN; TPM_TDI; B	2002/03/31 20:06
45	BRS	L45	16	44 and transistor	USPAT; US-PGP; UB; EPO; JPO; DERWEN; TPM_TDI; B	2002/03/31 20:06